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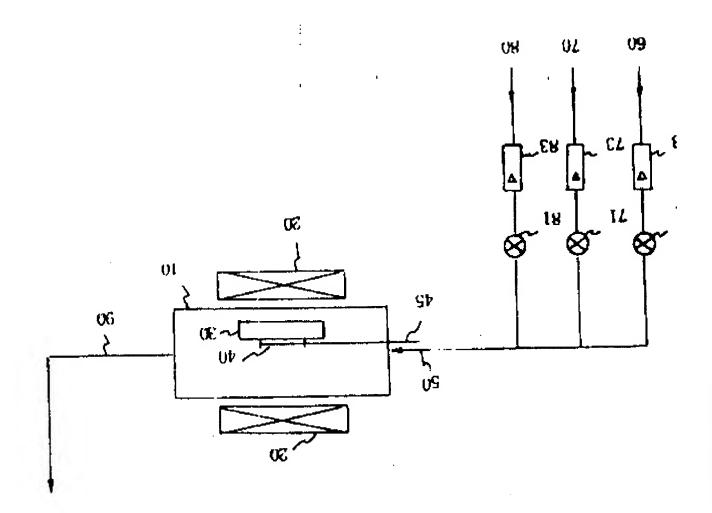
> AMORPHOUS SILICON (54) FORMATION OF FILM

(57) Abstract:

amorphous silicon film on a substrate gaseous silane by mixing the specific by thermal decomposition of higher PURPOSE: To form an amorphous silicon film at a low temp. and high group III compd. with the gaseous speed in the stage of forming the raw material.

disposed on the outside of the furnace Ga, In, etc. are mixed and the mixture etc. is put in a decomposition furnace of the group III compd. such as B, Al the heater 20 to decompose thermally Higher gaseous silane 60 such as amorphous silicon film is formed on consisting of silicon or quartz glass, same time heated to 100W600°C by SinH2n+2 (n>2 integer) and having 2, 3, 4 (n), carrier gas 70 such as Ar relatively low temp. and high speed. and hydride, halide, org. compd. 80 heater 20 of a halogen lamp, etc. is the surface of the substrate 40 at a is passed through the inside of the CONSTITUTION: A substrate 40 expressed by the general formula disilane, trisilane, tetrasilane, etc. furnace 10. The mixture is at the 10 formed of quartz glass and a the gaseous silane, by which

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